



### FEATURES

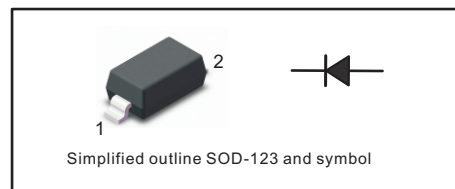
- For surface mounted applications
- Glass Passivated Chip Junction
- Fast reverse recovery time
- Ideal for automated placement
- Lead free in comply with EU RoHS 2011/65/EU directives

### MECHANICAL DATA

- Case: SOD-123
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 16mg/0. 00056oz

### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



### Absolute Maximum Ratings at 25 °C

Parameter	Symbols	T-1N4148W	Units
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	100	V
Maximum RMS voltage	$V_{RMS}$	75	V
Average Rectified Forward Current	$I_{F(AV)}$	150	mA
Non-reptitive Peak Forward Surge Current	$I_{FSM}$	0.5 1 4	A
		at 1s	
		at 1ms	
		at 1us	
Total Power Dissipation	$P_{tot}$	400	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 ~ +150	°C

### Characteristics at $T_a = 25\text{ °C}$

Parameter	Symbols	T-1N4148W	Units
Reverse Breakdown Voltage at $I_R = 1\mu A$	$V_{(BR)R}$	75	V
Maximum Forward Voltage	$V_F$	0.715 0.855 1.00 1.25	V
		at 1 mA	
		at 10 mA	
		at 50 mA	
		at 150 mA	
Peak Reverse Current	$I_R$	0.025 1 30 50	$\mu A$
		at $V_R = 20V$ $T_j = 25\text{ °C}$	
		at $V_R = 75V$ $T_j = 25\text{ °C}$	
		at $V_R = 25V$ $T_j = 150\text{ °C}$	
		at $V_R = 75V$ $T_j = 150\text{ °C}$	
Typical Junction Capacitance	$C_j$	2	pF
		f=1MHz, $V_R = 0V$	
Maximum Reverse Recovery Time <sup>(1)</sup>	$t_{rr}$	4	ns

(1) Measured with  $I_F = I_R = 10mA, I_{rr} = 0.1 \times I_R, R_L = 100\Omega$



Fig.1 Forward Current Derating Curve

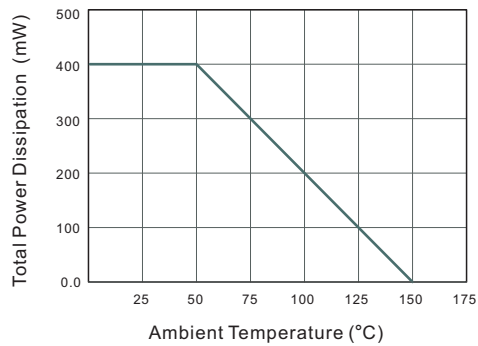


Fig.2 Typical Reverse Characteristics

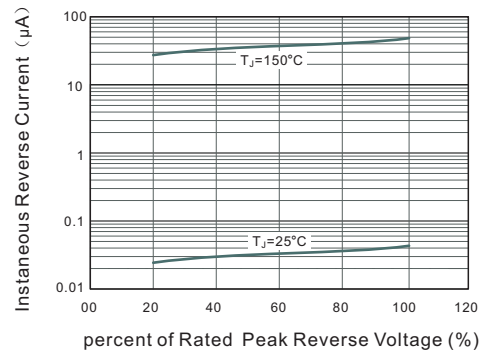


Fig.3 Typical Instantaneous Forward Characteristics

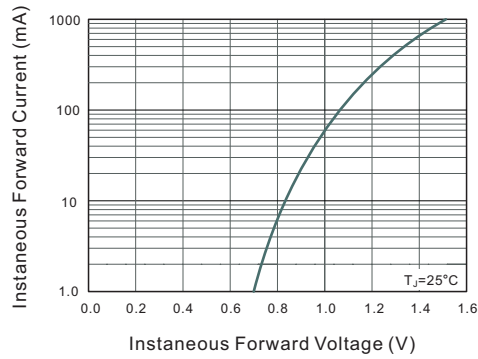
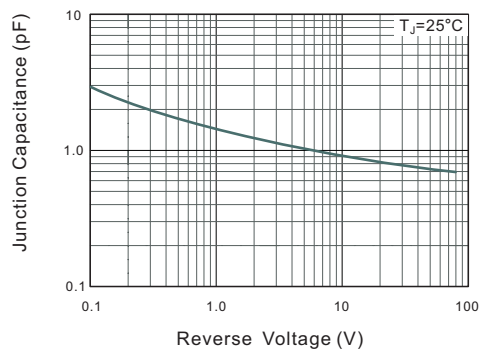


Fig.4 Typical Junction Capacitance

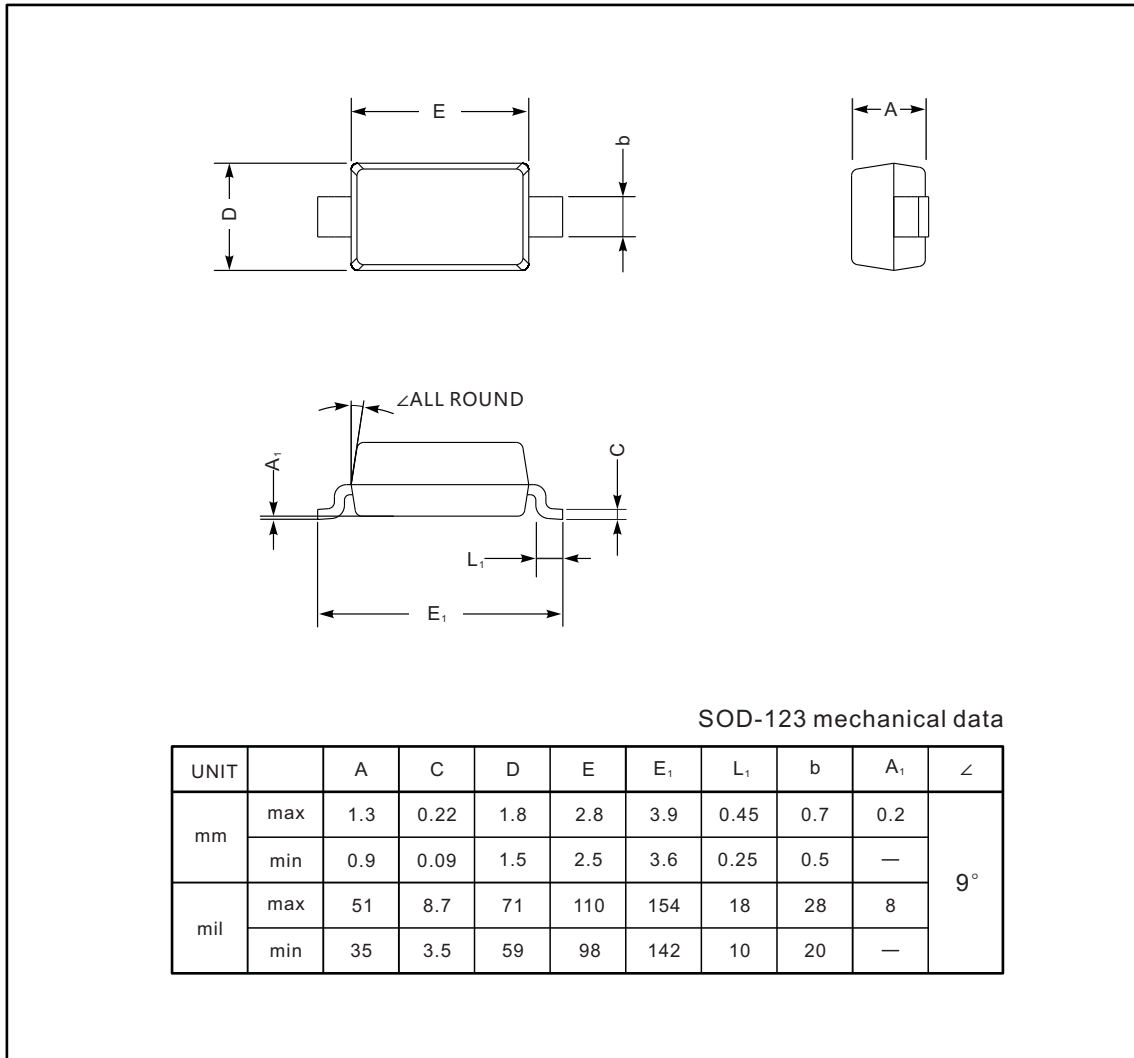




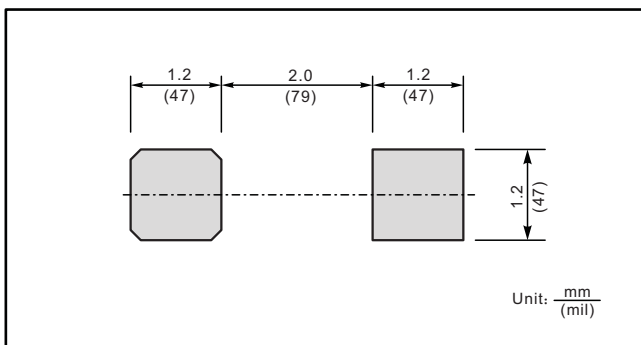
**PACKAGE OUTLINE**

Plastic surface mounted package; 2 leads

SOD-123



**The recommended mounting pad size**



**Marking**

Type number	Marking code
T-1N4148W	T4

单击下面可查看定价，库存，交付和生命周期等信息

[>>JINGDAO\(晶导微\)](#)